

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	35mΩ@-4.5V	-4.5A
	45mΩ@-2.5V	

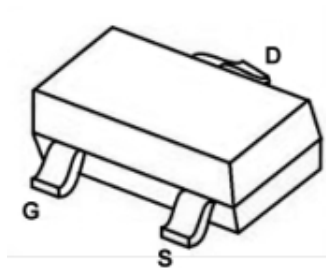
Feature

- TrenchFET Power MOSFET

Application

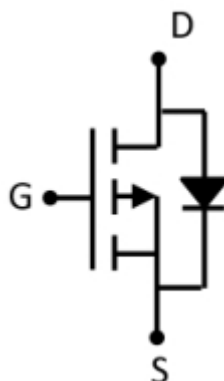
- PA Switch
- Load Switch

Package

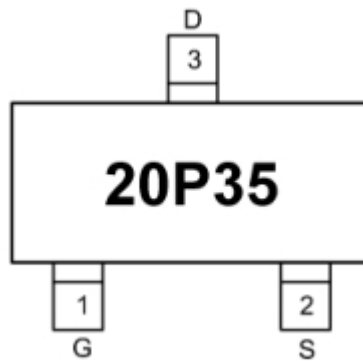


SOT-23

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4.5	A
Pulsed Drain Current	I_{DM}	-20	A
Power Dissipation	P_D	1.7	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	73.5	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

Electrical characteristics

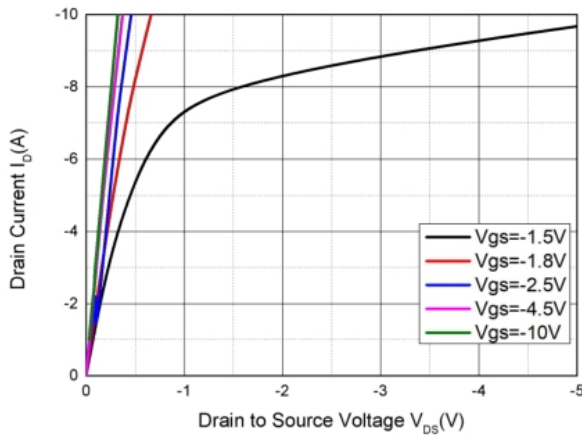
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	μA
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.75	-0.9	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3.3A$		35	57	m Ω
		$V_{GS} = -2.5V, I_D = -2.8A$		45	76	
		$V_{GS} = -1.8V, I_D = -2.3A$		55	110	
Dynamic Characteristics ²						
Input Capacitance ¹⁾²⁾	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1MHz$		686	960	pF
Output Capacitance ¹⁾²⁾	C_{oss}			90.8	127	
Reverse Transfer Capacitance ¹⁾²⁾	C_{rss}			80.4	113	
Total Gate Charge ¹⁾	Q_g	$V_{DS} = -15V, V_{DS} = -4.5V,$ $I_D = -3A$		9.7	13.6	pF
Gate-Source Charge ¹⁾	Q_{gs}			2.05	2.9	
Gate-Drain Charge ¹⁾	Q_{gd}			2.43	3.4	
Switching Characteristics ¹⁾²⁾						
Turn-On Delay Time	$T_{d(on)}$	$V_{GEN} = -4.5V, V_{DD} = -10V,$ $I_D = -3A, R_G = 3.3\Omega$		4.8	9.6	nS
Rise Time	T_r			9.6	17.3	
Turn-Off Delay Time	$T_{d(off)}$			52	104	
Fall Time	T_f			8.4	16.8	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = -1A$		-0.77	-1	V

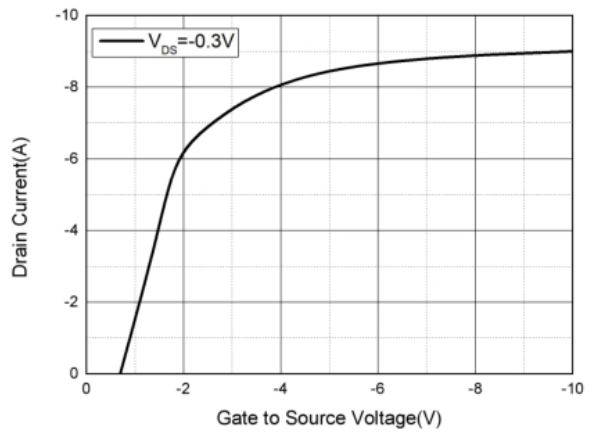
Note:

1. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. These parameters have no way to verify.

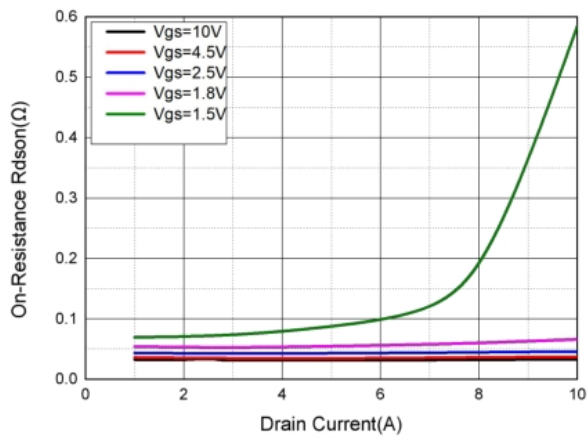
Typical Characteristics



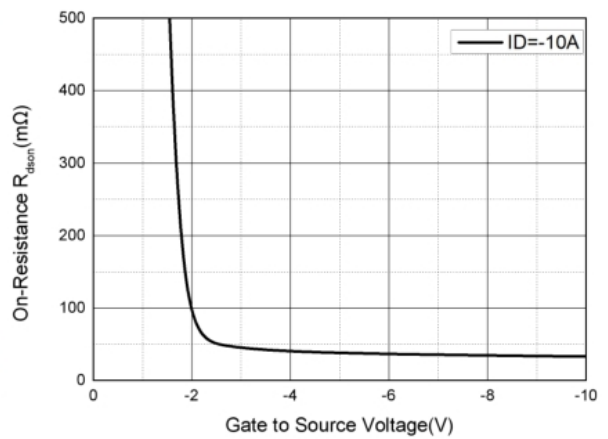
Output Characteristics



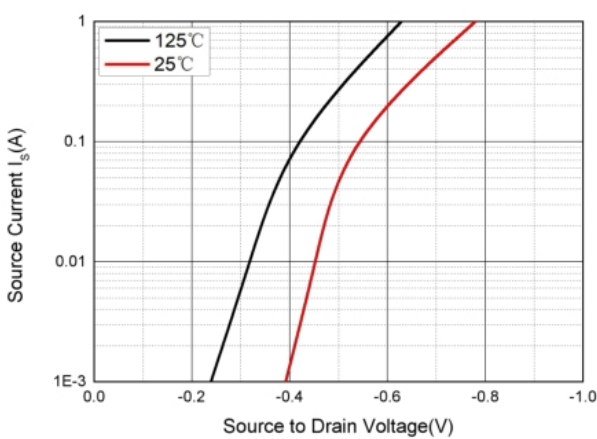
Transfer Characteristics



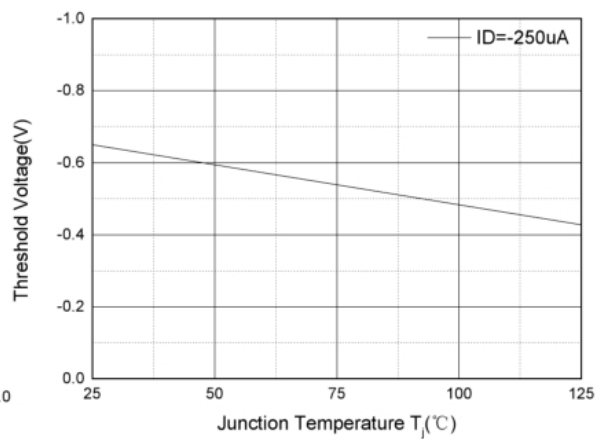
$R_{DS(on)}$ vs. I_D



$R_{DS(on)}$ vs. V_{GS}

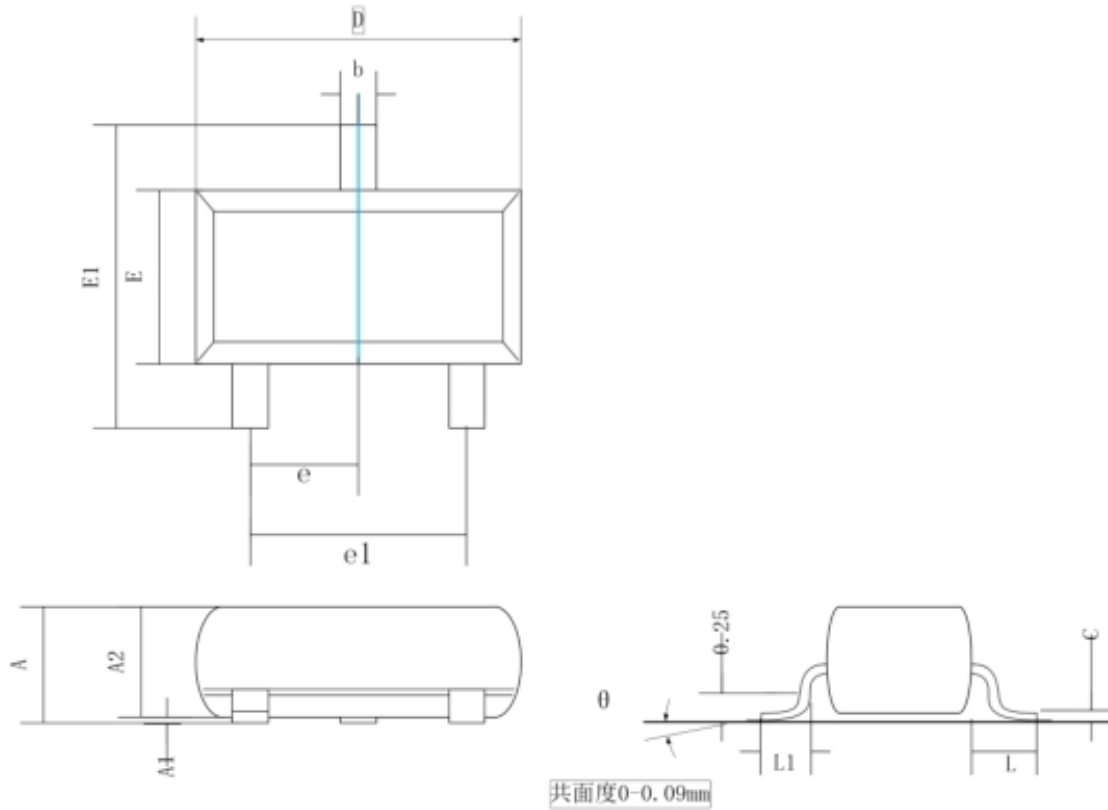


I_S vs. V_{SD}



Threshold Voltage

SOT-23-3L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°